MCH3486

Power MOSFET 60V, 137mΩ, 2A, Single N-Channel

Features

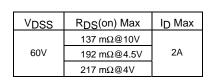
- Low RDS(on)
- 4V Drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS Compliance
- Small Surface Mount Package (MCPH3)

Specifications

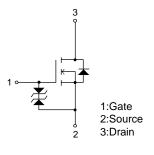
Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	60	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	۱ _D	2	А
Drain Current (Pulse) PW≤10µs, duty cycle≤1%	I _{DP}	8	A
Power Dissipation When mounted on ceramic substrate (900mm ² ×0.8mm)	PD	1	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

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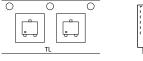


Packing Type:TL

Marking

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm ² ×0.8mm)	R _{θJA}	125	°C/W





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

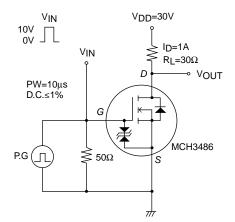
See detailed ordering and shipping information on page 5 of this data sheet.

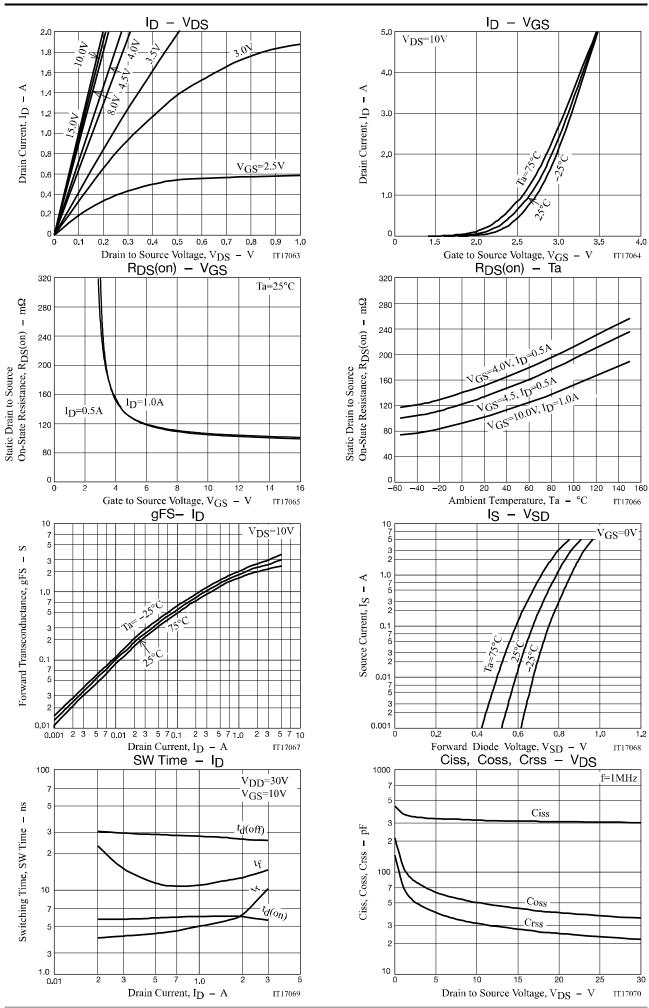
Electrical Characteristics at $Ta = 25^{\circ}C$

Parameter	Cumhol	Conditions		Value		11.3
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	60			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =60V, V _{GS} =0V			1	μA
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μA
Gate Threshold Voltage	VGS(th)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =1A		1.8		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =1A, V _{GS} =10V		105	137	mΩ
	R _{DS} (on)2	I _D =0.5A, V _{GS} =4.5V		137	192	mΩ
	R _{DS} (on)3	I _D =0.5A, V _{GS} =4V		155	217	mΩ
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		310		pF
Output Capacitance	Coss			40		pF
Reverse Transfer Capacitance	Crss			25		pF
Turn-ON Delay Time	t _d (on)			6		ns
Rise Time	tr			5		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		28		ns
Fall Time	tf			11		ns
Total Gate Charge	Qg	V _{DS} =30V, V _{GS} =10V, I _D =2A		7		nC
Gate to Source Charge	Qgs			1		nC
Gate to Drain "Miller" Charge	Qgd	1		1.3		nC
Forward Diode Voltage	V _{SD}	IS=2A, VGS=0V		0.83	1.2	V

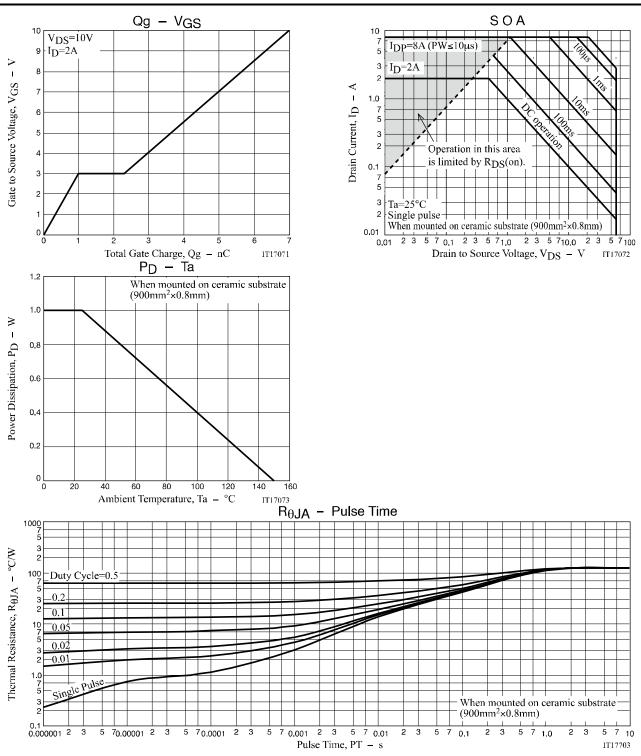
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit





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Package Dimensions

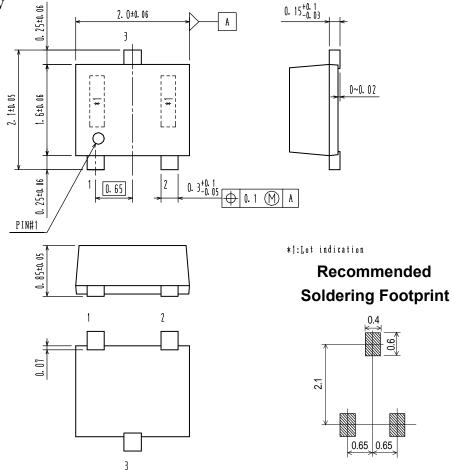
MCH3486-TL-H/ MCH3486-TL-W

MCPH3

CASE 419AQ ISSUE O

Unit : mm

- 1 : Gate
- 2 : Source
- 3 : Drain



Ordering & Package Information

Device	Package	Shipping	Note	
MCH3486-TL-H	MCPH3	2.000 ppg. / rool	Pb-Free	
MCH3486-TL-W	SC-70,SOT-323	3,000 pcs. / reel	and Halogen Free	

Note on usage : Since the MCH3486 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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